SEMICONDUCTOR DEVICE HAVING REDUCED CAPACITANCE TO SUBSTRATE AND METHOD

Abstract of the Disclosure

In one embodiment, a matrix of free-standing semiconductor shapes are oxidized to form a low capacitance isolation tub. The adjacent rows of shapes in the matrix are offset with respect to each to minimize air gap and void formation during tub formation. In a further embodiment, the spacing between adjacent rows is less than the spacing between shapes within a row.